Siegfried Hofmann

List of Publications by Year
in descending order

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46	2,435	304743 22	223800 46
papers	citations	h-index	g-index

47	47	47	1201
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Artifacts in multilayer depth profiling: Origin and quantification of a double peak layer profile of Ag in ToF-SIMS depth profiles of an Ag/Ni multilayer. Materials Characterization, 2021, 171, 110774.	4.4	2
2	Entropy matters in grain boundary segregation. Acta Materialia, 2021, 206, 116597.	7.9	21
3	Prediction and experimental determination of the layer thickness in SIMS depth profiling of Ge/Si multilayers: Effect of preferential sputtering and atomic mixing. Applied Surface Science, 2019, 481, 1103-1108.	6.1	3
4	Preferential sputtering effects in depth profiling of multilayers with SIMS, XPS and AES. Applied Surface Science, 2019, 483, 140-155.	6.1	14
5	The Significance of Entropy in Grain Boundary Segregation. Materials, 2019, 12, 492.	2.9	14
6	Depth resolution and preferential sputtering in depth profiling of delta layers. Applied Surface Science, 2018, 455, 1045-1056.	6.1	8
7	Correlation of depth resolution and preferential sputtering in depth profiles of thin layers by Secondary Ion Mass Spectrometry (SIMS). Thin Solid Films, 2018, 662, 165-167.	1.8	3
8	Depth resolution and preferential sputtering in depth profiling of sharp interfaces. Applied Surface Science, 2017, 410, 354-362.	6.1	21
9	Depth resolution in sputter profiling revisited. Surface and Interface Analysis, 2016, 48, 1354-1369.	1.8	17
10	Interstitial and substitutional solute segregation at individual grain boundaries ofÎ±-iron: data revisited. Journal of Physics Condensed Matter, 2016, 28, 064001.	1.8	22
11	Quantitative reconstruction of Ta/Si multilayer depth profiles obtained by Time-of-Flight-Secondary-Ion-Mass-Spectrometry (ToF-SIMS) using Cs+ ion sputtering. Thin Solid Films, 2015, 591, 60-65.	1.8	8
12	Quantitative reconstruction of the GDOES sputter depth profile of a monomolecular layer structure of thiourea on copper. Applied Surface Science, 2015, 331, 140-149.	6.1	19
13	Applied Thermodynamics: Grain Boundary Segregation. Entropy, 2014, 16, 1462-1483.	2.2	38
14	Analytical and numerical depth resolution functions in sputter profiling. Applied Surface Science, 2014, 314, 942-955.	6.1	25
15	Sputter depth profiling: past, present, and future. Surface and Interface Analysis, 2014, 46, 654-662.	1.8	22
16	Quantitative Compositional Depth Profiling. Springer Series in Surface Sciences, 2013, , 297-408.	0.3	8
17	Influence of non-Gaussian roughness on sputter depth profiles. Applied Surface Science, 2013, 276, 447-453.	6.1	16
18	An analytical depth resolution function for the MRI model. Surface and Interface Analysis, 2013, 45, 1659-1660.	1.8	10

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19	Influence of nonstationary atomic mixing on depth resolution in sputter depth profiling. Surface and Interface Analysis, 2012, 44, 569-572.	1.8	16
20	Thermodynamics of Grain Boundary Segregation and Applications to Anisotropy, Compensation Effect and Prediction. Critical Reviews in Solid State and Materials Sciences, 2008, 33, 133-163.	12.3	64
21	Backscattering effect in quantitative AES sputter depth profiling of multilayers. Surface and Interface Analysis, 2007, 39, 787-797.	1.8	15
22	Characterization of nanolayers by sputter depth profiling. Applied Surface Science, 2005, 241, 113-121.	6.1	42
23	Quantitative AES depth profiling of a Ge/Si multilayer structure. Surface and Interface Analysis, 2002, 33, 461-471.	1.8	15
24	Determination of the Depth Scale in Sputter Depth Profiling. Journal of Surface Analysis (Online), 2002, 9, 306-309.	0.1	22
25	Quantitative comparison between Auger electron spectroscopy and secondary ion mass spectroscopy depth profiles of a double layer structure of AlAs in GaAs using the mixing-roughness-information depth model. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 1111-1115.	2.1	15
26	Ultimate depth resolution and profile reconstruction in sputter profiling with AES and SIMS. Surface and Interface Analysis, 2000, 30, 228-236.	1.8	76
27	Original and sputtering induced interface roughness in AES sputter depth profiling of SiO 2 /Ta 2 O 5 multilayers. Thin Solid Films, 1999, 355-356, 390-394.	1.8	17
28	From depth resolution to depth resolution function: refinement of the concept for delta layers, single layers and multilayers. Surface and Interface Analysis, 1999, 27, 825-834.	1.8	74
29	Ultrahigh Resolution in Sputter Depth Profiling with Auger Electron Spectroscopy Using Ionized SF6 Molecules as Primary Ions. Japanese Journal of Applied Physics, 1998, 37, L758-L760.	1.5	12
30	Determination and application of the depth resolution function in sputter profiling with secondary ion mass spectroscopy and Auger electron spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 1096-1102.	2.1	35
31	Structural surface phase transitions during segregation competition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 1493-1496.	2.1	4
32	Thermodynamics and structural aspects of grain boundary segregation. Critical Reviews in Solid State and Materials Sciences, 1995, 20, 1-85.	12.3	226
33	Atomic mixing, surface roughness and information depth in high-resolution AES depth profiling of a GaAs/AlAs superlattice structure. Surface and Interface Analysis, 1994, 21, 673-678.	1.8	170
34	Approaching the limits of high resolution depth profiling. Applied Surface Science, 1993, 70-71, 9-19.	6.1	81
35	Interlaboratory comparison of the depth resolution in sputter depth profiling of Ni/Cr multilayers with and without sample rotation using AES, XPS, and SIMS. Surface and Interface Analysis, 1993, 20, 621-626.	1.8	61
36	Cascade mixing limitations in sputter profiling. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 316.	1.6	63

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37	Compositional depth profiling by sputtering. Progress in Surface Science, 1991, 36, 35-87.	8.3	101
38	Determination of the atomic mixing layer in sputter profiling of Ta/Si multilayers by TEM and AES. Surface and Interface Analysis, 1990, 15, 794-796.	1.8	40
39	Redeposition in AES sputter depth profiling of multilayer Cr/Ni thin films. Surface and Interface Analysis, 1988, 12, 83-86.	1.8	24
40	Preferential sputtering of oxides: A comparison of model predictions with experimental data. Applied Surface Science, 1986, 27, 355-365.	6.1	245
41	Practical surface analysis: state of the art and recent developments in AES, XPS, ISS and SIMS. Surface and Interface Analysis, 1986, 9, 3-20.	1.8	106
42	Depth Resolution and Quantitative Evaluation of AES Sputtering Profiles. Topics in Current Physics, 1984, , 141-158.	0.5	24
43	The statistical sputtering contribution to resolution in concentration-depth profiles. Thin Solid Films, 1981, 81, 239-246.	1.8	74
44	Quantitative depth profiling in surface analysis: A review. Surface and Interface Analysis, 1980, 2, 148-160.	1.8	292
45	Depth resolution and surface roughness effects in sputter profiling of NiCr multilayer sandwich samples using Auger electron spectroscopy. Thin Solid Films, 1977, 43, 275-283.	1.8	98
46	Evaluation of concentration-depth profiles by sputtering in SIMS and AES. Applied Physics Berlin, 1976, 9, 59-66.	1.4	151